# XP0NG8A

# Silicon PNP epitaxial planar type (Tr) Silicon epitaxial planar type (SWD)

For digital circuits

#### Features

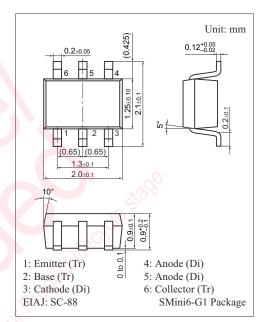
- Two elements incorporated into one package (Tr + SWD)
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts
- SMini type package allowing easy automatic insertion through tape packing and magazine packing

#### Basic Part Number

• UNR211L + MA3X152E

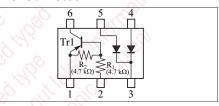
## Absolute Maximum Ratings $T_a = 25^{\circ}C$

	Parameter	Symbol	Rating	Unit	
Tr	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V	
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	v	
	Collector current	I <sub>C</sub>	-100	mA	
SWD	Forward current	I <sub>F</sub>	100	mA	
	Peak forward current	I <sub>FM</sub>	225	mA	
	Non-repetitive peak forward surge current *	I <sub>FSM</sub>	500	mA	
	Reverse voltage	VR	80	VV	
	Maximum peak reverse voltage	V <sub>RM</sub>	80	No. V	
Overall	Total power dissipation	P <sub>T</sub>	150	mW	
	Junction temperature	Tj	150	°C <<	
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C	
Note) *: t	=1s		Q163.	e nite	



#### Marking Symbol: 4D

#### Internal Connection



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## Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

• Tr

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu {\rm A}, \ I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2  {\rm mA},  I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{\rm EB} = -6$ V, $I_{\rm C} = 0$			-2.0	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	20			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{\rm CC} = -5 \text{ V}, V_{\rm B} = -0.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{\rm CC} = -5 \text{ V}, V_{\rm B} = -2.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R <sub>1</sub>		- <mark>3</mark> 0%	4.7	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.8	1.0	1.2	_
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$	E.	80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### • SWD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	V <sub>F</sub>	$I_F = 100 \text{ mA}$			1.2	V
Reverse voltage	V <sub>R</sub>	$I_R = 100 \ \mu A$	80		10	V
Reverse current	I <sub>R</sub>	$V_R = 75 V$	8		0.1	μΑ
Terminal capacitance	Ct	$V_{R} = 0 V, f = 1 MHz$	Ser l	02	2.0	pF
Reverse recovery time	t <sub>rr</sub>	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω, $I_{rr} = 0.1$ $I_R$			3.0	ns

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

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